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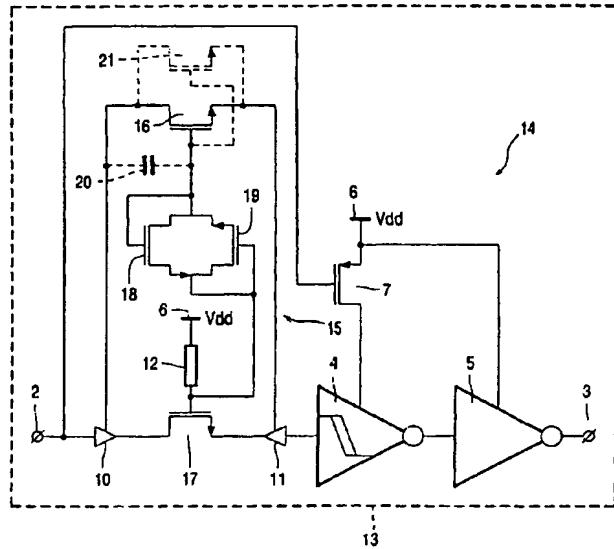
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*[Continued on next page]*

(54) Title: A VOLTAGE LIMITING SEMICONDUCTOR PASS GATE CIRCUIT



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(57) Abstract: A voltage limiting semiconductor pass gate circuit (15), comprises a first transistor (16), operatively connected to an input node (10) and an output node (11) of the pass gate circuit (15), and a second transistor (17), operatively connected between the input node (10) and the output node (11). The second transistor (17) has a control electrode biased to a supply voltage (6), and the first transistor (16) has a control electrode which connects by two back-to-back connected diode elements (18, 19) to the control electrode of the second transistor (17). The pass gate circuit (15) is typically applied in input I/O cells (14) of semiconductor integrated circuits (13).